

**Silicon NPN Power Transistors**

**BUL6825**

**DESCRIPTION**

- With TO-220C package
- High voltage ,high speed

**APPLICATIONS**

- Relay drivers
- Inverters
- Switching regulators
- Deflection circuits

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

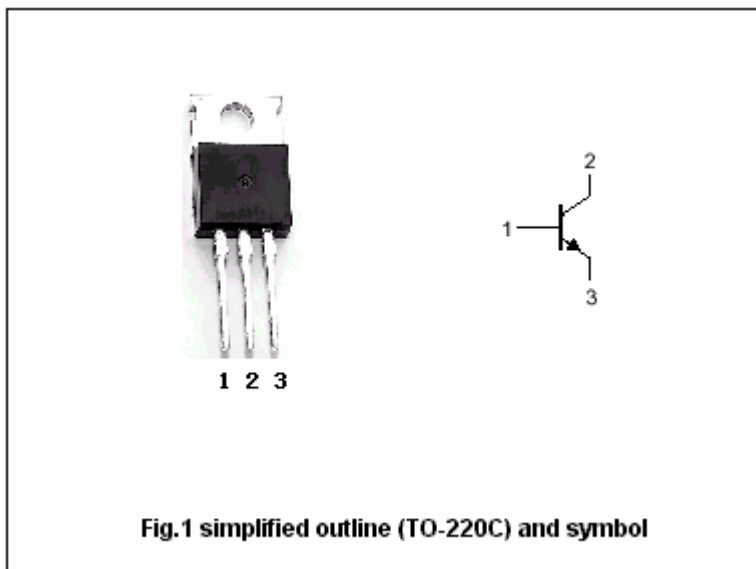


Fig.1 simplified outline (TO-220C) and symbol

**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	700	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	9	V
I <sub>C</sub>	Collector current (DC)		4	A
I <sub>CM</sub>	Collector current-Peak		8	A
I <sub>B</sub>	Base current		2	A
I <sub>BM</sub>	Base current-Peak		4	A
P <sub>D</sub>	Total power dissipation	T <sub>a</sub> =25	2	W
		T <sub>C</sub> =25	75	
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-65~150	

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	1.67	/W

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**CHARACTERISTICS**

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	400			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1A ; I <sub>B</sub> =0.2A			0.5	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A ; I <sub>B</sub> =0.5A T <sub>C</sub> =100			0.6 1.0	V
V <sub>CEsat-3</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =1A			1.0	V
V <sub>BEsat-1</sub>	Base-emitter saturation voltage	I <sub>C</sub> =1A ; I <sub>B</sub> =0.2A			1.2	V
V <sub>BEsat-2</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A ; I <sub>B</sub> =0.5A T <sub>C</sub> =100			1.6 1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =700V ; I <sub>E</sub> =0 T <sub>C</sub> =100			1.0 5.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =9V ; I <sub>C</sub> =0			1.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	10		60	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =5V	8		40	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =5V	4			MHz
C <sub>OB</sub>	Collector outoput capacitance	f=1MHz ; V <sub>CB</sub> =10V		65		pF

Switching times resistive load

t <sub>d</sub>	Delay time	V <sub>CC</sub> =125V , I <sub>C</sub> =2A I <sub>B1</sub> =- I <sub>B2</sub> =0.4A t <sub>p</sub> =25 μ s duty cycle 1%			0.1	μ s
t <sub>r</sub>	Rise time				0.7	μ s
t <sub>s</sub>	Storage time				4.0	μ s
t <sub>f</sub>	Fall time				0.9	μ s

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PACKAGE OUTLINE

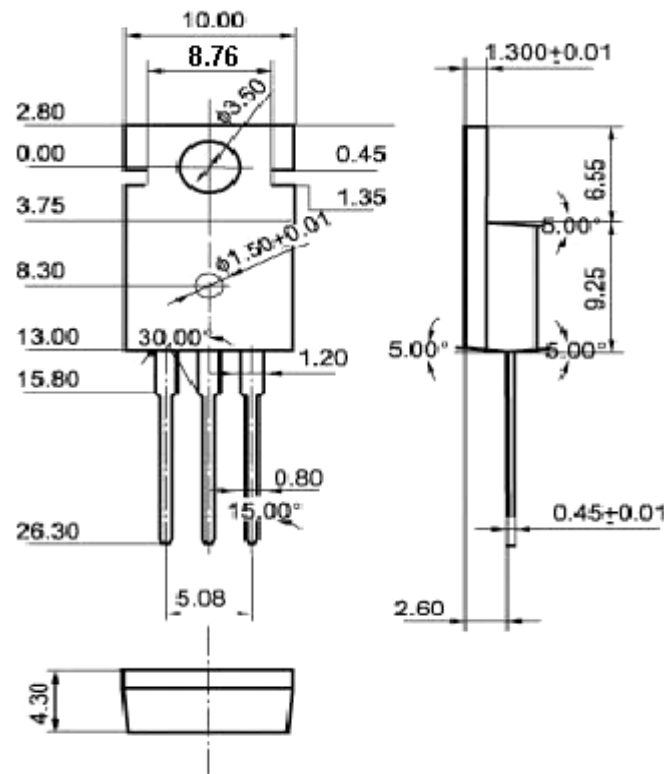


Fig.2 Outline dimensions (unindicated tolerance: 0.1mm)